

Title (en)

METHOD FOR PROVIDING A SILICIDE ELECTRODE ON A SUBSTRATE SUCH AS A SEMICONDUCTOR SUBSTRATE

Publication

EP 0000317 B1 19820519 (FR)

Application

EP 78430003 A 19780622

Priority

US 81191477 A 19770630

Abstract (en)

[origin: US4180596A] A method for providing on a substrate a layer of a metal silicide such as molybdenum silicide and/or tantalum silicide and/or tungsten silicide and/or rhodium silicide which includes coevaporating silicon and the respective metal onto a substrate, and then heat treating the substrate to form the metal silicide.

IPC 1-7

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IPC 8 full level

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CPC (source: EP US)

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Cited by

EP0096773A3; EP0100454A1; FR2458900A1; EP0024905A3; EP0132720A1; EP0466166A1; US5256894A; EP0022474A1; EP0219827A3; EP0224199A1; EP0207486A1; EP0090318A3; FR2489591A1; EP0017697A1

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